

ABSTRACT OF THE DISCLOSURE

There is provided a semiconductor laser device having on a single substrate a plurality of laser portions each oscillating laser light of a different wavelength, the plurality of laser portions containing different types, respectively, of dopant. There is also provided a method of fabricating a semiconductor laser device, forming on a single substrate a plurality of laser portions each oscillating laser light of a different wavelength, initially forming a laser portion in a crystal growth method and subsequently forming another laser portion in a different crystal growth method.

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